IN THE SPECIFICATION:

Please amend paragraphs [0020] and [0029] as follows:

[0020] FIG. 1 is a cross-section of one embodiment of a processing chamber 10 of the invention adapted for processing substrates. The processing chamber 10 comprises a body 12 and a lid 14 disposed on the body 12. The processing chamber 10 defines a cavity that includes a processing region 16 therein. A gas dispersion plate (e.g., a showerhead) 18 is mounted to the lid 14 and defines the upper boundary of the processing region 16. A plurality of holes 20 are formed in the gas dispersion plate 18 to allow delivery of processing gases therethrough and into the chamber. Although, in one aspect the gas dispersion plate 18 also acts as an anode coupled to an RF generator 15 and matching network 17 to supply RF energy to the processing region 16, other anodes such as plates, electrodes, and antennas may be used to deliver the RF energy to the processing region 16. The chamber 10 also includes a movable substrate support member 32, also referred to as a susceptor, which can be raised or lowered in the chamber by a motor 33. The substrate support member 32 is typically heated using ~~restive~~ resistive heaters, lamps, or other heating devices commonly used in the field of electronic device fabrication. The heated substrate support member therefore includes a heater to heat a substrate 28. A vacuum pump 19 is coupled to the chamber 10 to control the chamber pressure therein.

[0029] In one process, an about 600mm x 720mm substrate 28 was positioned on a support member 32 having an insulating layer 50 disposed thereon. The insulating layer 50 is formed of aluminum oxide and is between about 125 mils and about 500 mils thick. The insulating layer 50 is positioned on the support member ~~28~~ 32 and held in place under its own weight. The substrate 28 is positioned on the insulating layer 50 and the support member 32 is moved into a processing position where an edge frame 22 is supported on the perimeter of the insulating layer 50 outwardly of the edge of the substrate exposing the

entire substrate 28. SiH_4 is introduced at a flow rate of between about 260sccm and 720sccm, NH_3 is introduced at a flow rate of between about 900sccm and 4000sccm, and N_2 is introduced into the chamber 10 at a flow rate of between about 5000sccm and 20000sccm through the gas dispersion plate 18. The chamber power level is set to between about 200watts and about 2900watts. The chamber is maintained at a pressure of between about 1.0 Torr and about 3.0 Torr by the vacuum pump 19. The spacing between the anode (*i.e.*, gas dispersion plate 18) and the substrate 28 is about 400mils to about 1500mils. The process temperature of the substrate 28 is about between 200°C and about 450°C. A SiN film was deposited on the substrate 28 at a deposition rate of about 500 to about 3000 angstroms/minute.